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P1 98.2

MOS FIELD EFFECT POWER TRANSISTOR

2SK1988, 1989

SWITCHING

N-CHANNEL POWER MOS FET

INDUSTRIAL USE

DESCRIPTION

The 2SK1988, 1989 is N-channel MOS Field Effect Transistor designed for high voltage switching applications.

FEATURES

- Low On-state Resistance
 2SK1988 $R_{DS(on)} = 2.8 \Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 1.5 \text{ A)}$
 2SK1989 $R_{DS(on)} = 3.0 \Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 1.5 \text{ A)}$
- Low C_{iss} $C_{iss} = 350 \text{ pF TYP.}$
- Built-in G-S Gate Protection Diode
- High Avalanche Capability Ratings

QUALITY GRADE

Standard

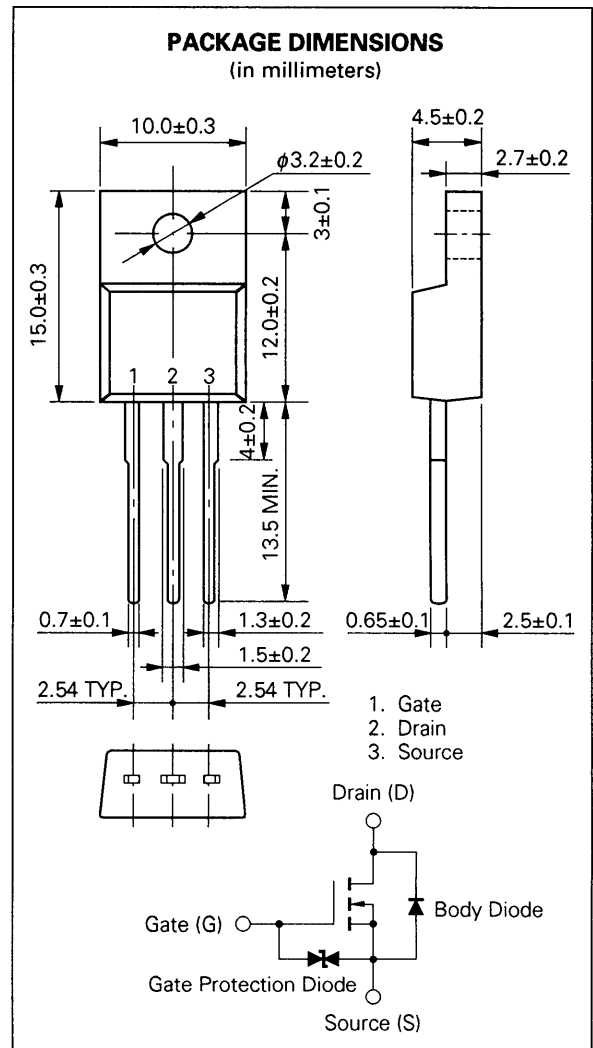
Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Drain to Source Voltage	V_{DSS}	450/500	V
Gate to Source Voltage	V_{GSS}	± 30	V
Drain Current (DC)	$I_{D(DC)}$	± 2.5	A
Drain Current (pulse)	$I_{D(pulse)^*}$	± 10	A
Single Avalanche Current	I_{AS}	3.75	A
Single Avalanche Energy	E_{AS}	73.8	mJ
Total Power Dissipation ($T_c = 25^\circ\text{C}$)	P_{T1}	30	W
Total Power Dissipation ($T_a = 25^\circ\text{C}$)	P_{T2}	2.0	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

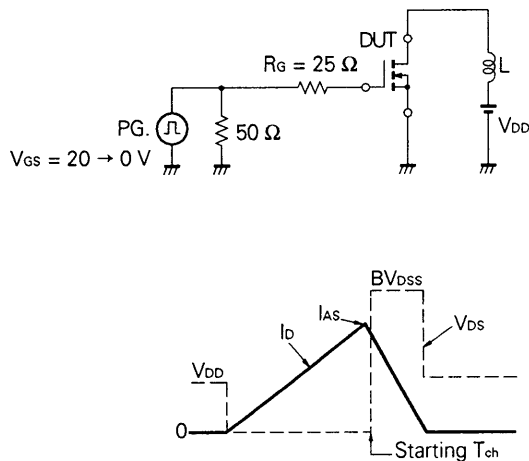
** Starting $T_{ch} = 25^\circ\text{C}$, $R_G = 25 \Omega$, $V_{GS} = 20 \text{ V} \rightarrow 0$



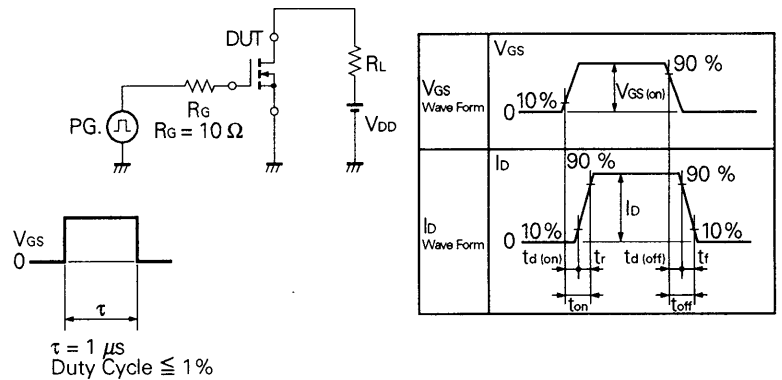
ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain to Source On-state Resistance (2SK1988)	R _{DS(on)}		2.2	2.8	Ω	V _{GS} = 10 V, I _D = 1.5 A
Drain to Source On-state Resistance (2SK1989)	R _{DS(on)}		2.4	3.0	Ω	V _{GS} = 10 V, I _D = 1.5 A
Gate to Source Cutoff Voltage	V _{GS(off)}	2.5		3.5	V	V _{DS} = 10 V, I _D = 1 mA
Forward Transfer Admittance	y _{fs}	0.9			S	V _{DS} = 10 V, I _D = 1.5 A
Drain Leakage Current	I _{DSS}			100	μA	V _{DS} = 450/500 V, V _{GS} = 0
Gate to Source Leakage Current	I _{GSS}			±10	μA	V _{GS} = ±30 V, V _{DS} = 0
Input Capacitance	C _{iss}		350		pF	V _{DS} = 10 V V _{GS} = 0 f = 1 MHz
Output Capacitance	C _{oss}		120		pF	
Reverse Transfer Capacitance	C _{rss}		45		pF	
Turn-On Delay Time	t _{d(on)}		10		ns	V _{GS} = 10 V V _{DD} = 150 V I _D = 1.5 A, R _G = 10 Ω R _L = 100 Ω
Rise Time	t _r		10		ns	
Turn-Off Delay Time	t _{d(off)}		30		ns	
Fall Time	t _f		10		ns	
Total Gate Charge	Q _G		12		nC	V _{GS} = 10 V I _D = 2.5 A V _{DD} = 400 V
Gate to Source Charge	Q _{GS}		3.0		nC	
Gate to Drain Charge	Q _{GD}		7.0		nC	
Diode Forward Voltage	V _{F(S-D)}		0.9		V	I _F = 2.5 A, V _{GS} = 0
Reverse Recovery Time	t _{rr}		310		ns	I _F = 2.5 A
Reverse Recovery Charge	Q _{rr}		1.2		μC	di/dt = 50 A/μs

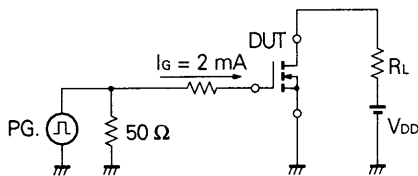
Test Circuit 1: Avalanche Capability



Test Circuit 2: Switching Time

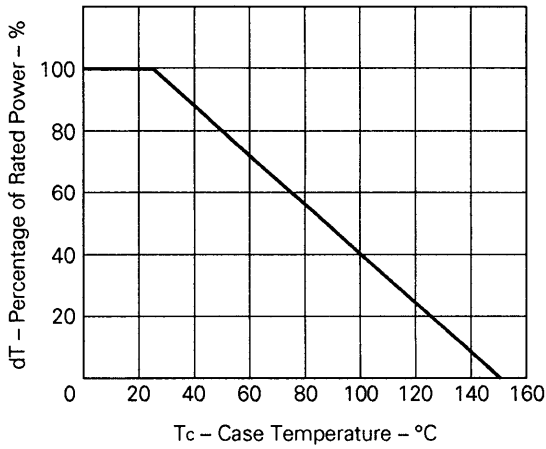


Test Circuit 3: Gate Charge

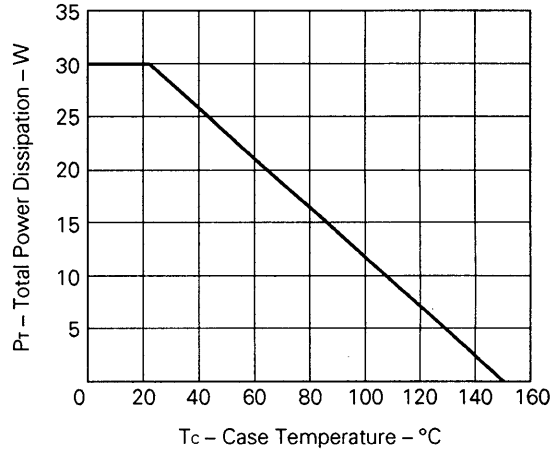


TYPICAL CHARACTERISTICS ($T_a = 25\text{ }^\circ\text{C}$)

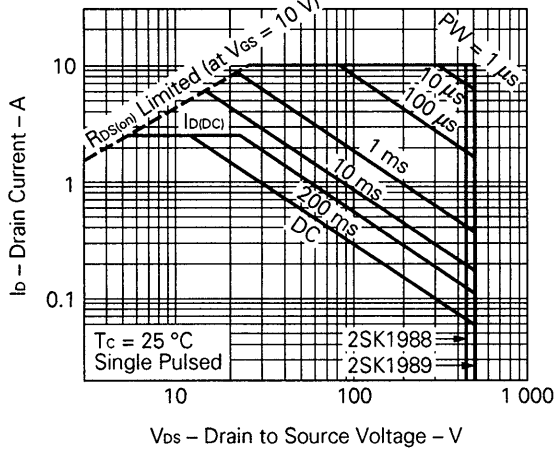
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



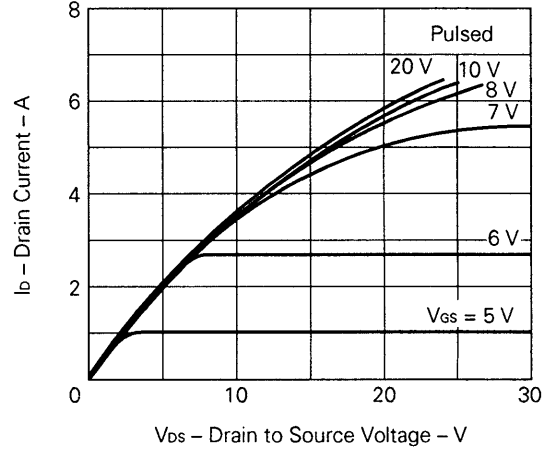
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



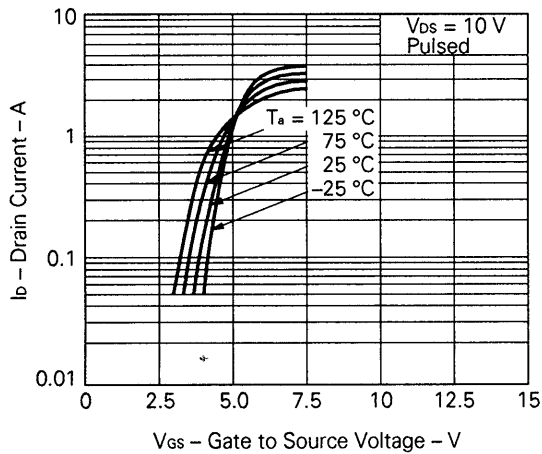
FORWARD BIAS SAFE OPERATING AREA



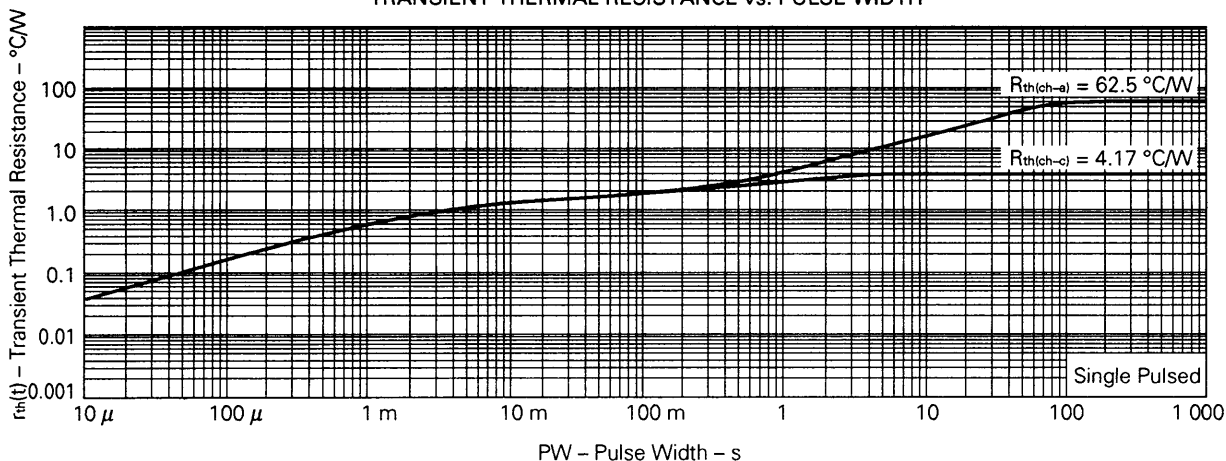
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



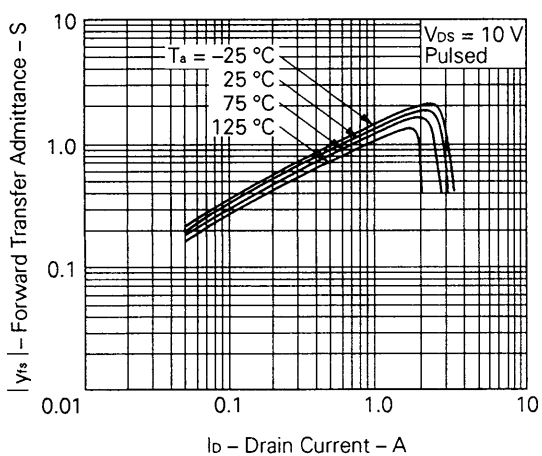
TRANSFER CHARACTERISTICS



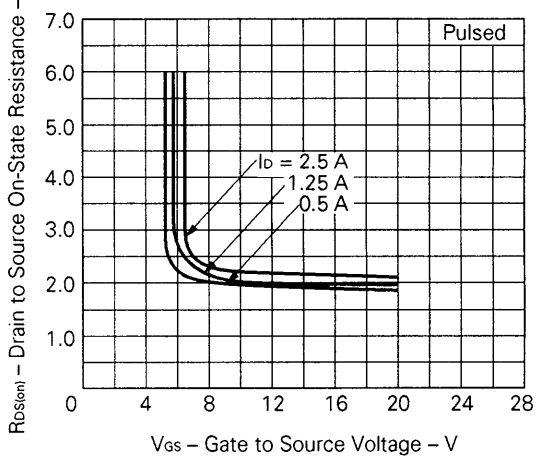
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



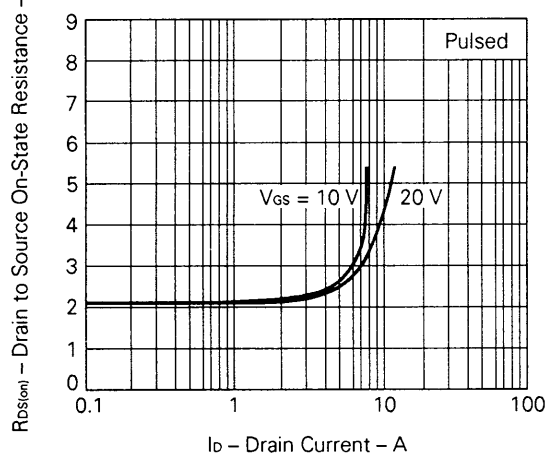
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



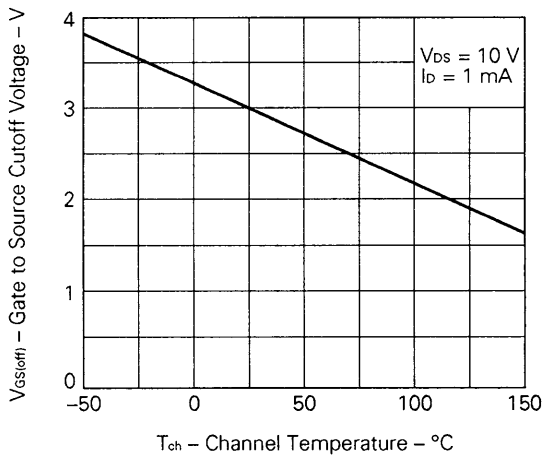
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

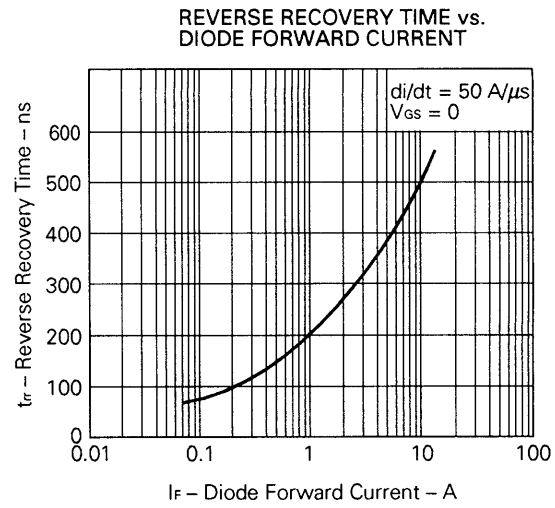
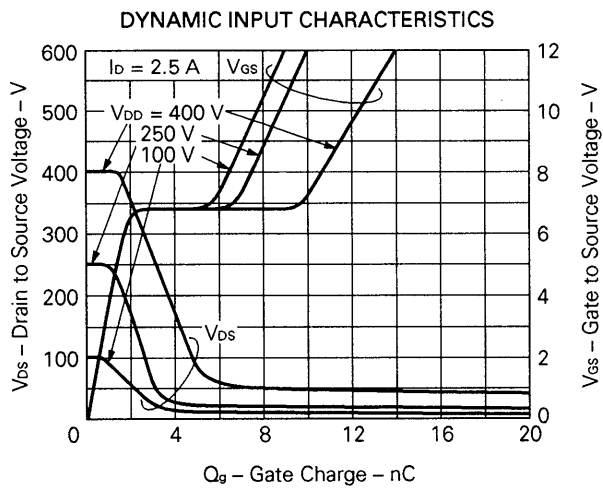
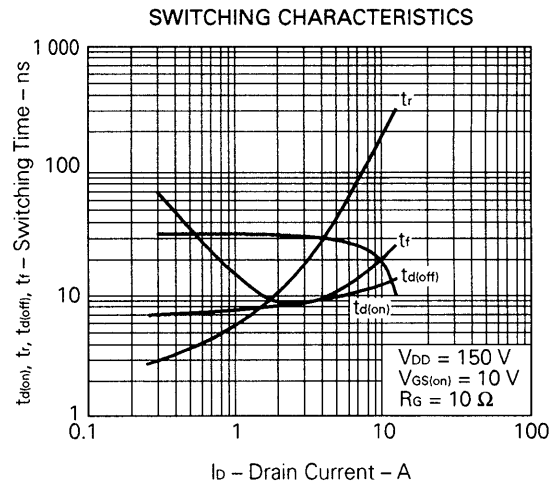
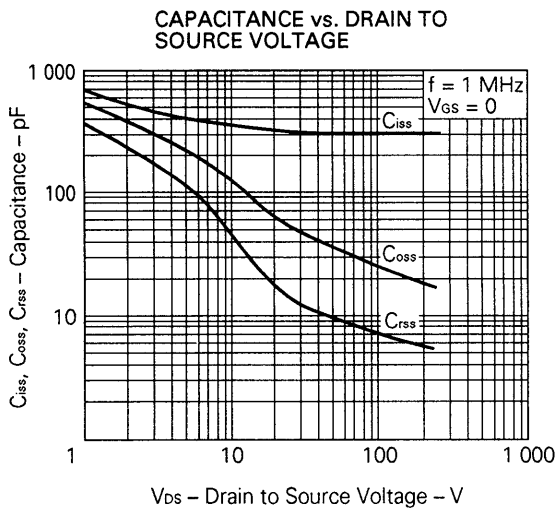
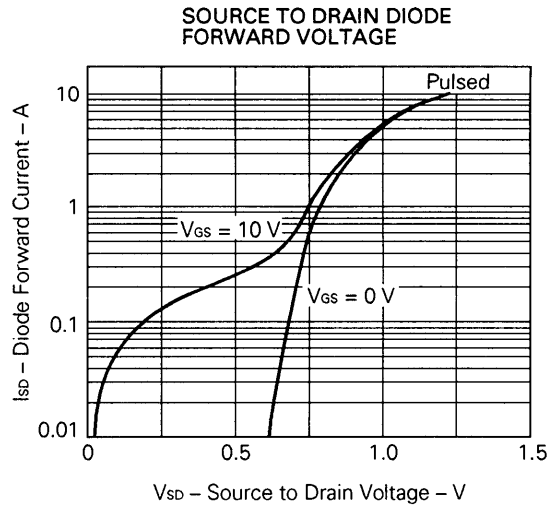
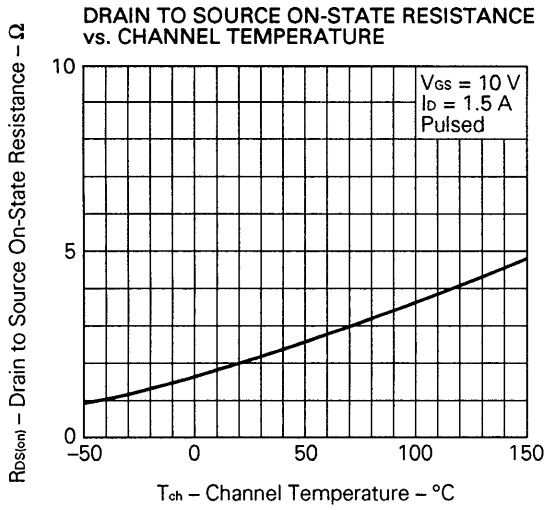


DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

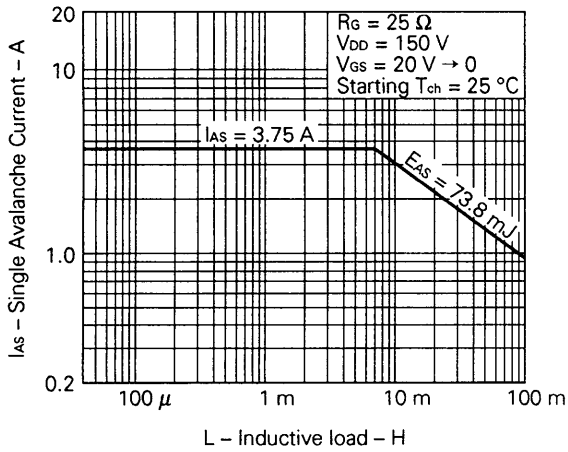


GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE

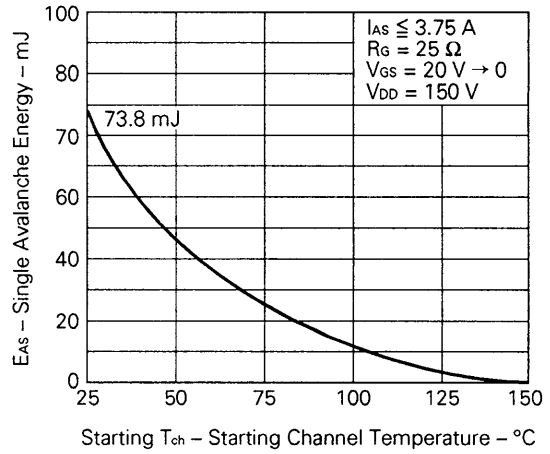




SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD



SINGLE AVALANCHE ENERGY vs. STARTING CHANNEL TEMPERATURE



Reference

Application note name	No.
Safe operating area of Power MOS FET.	TEA-1034
Application circuit using Power MOS FET.	TEA-1035
Quality control of NEC semiconductors devices.	TEI-1202
Quality control guide of semiconductors devices.	MEI-1202
Assembly manual of semiconductors devices.	IEI-1207

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